

IPD320N20N3GATMA1

IPD320N20N3GATMA1 Information



For Reference Only

Part Number IPD320N20N3GATMA1
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 200V 34A

Package TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

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IPD320N20N3GATMA1 Specifications

Manufacturer Part NumberIPD320N20N3GATMA1ManufacturerInfineon TechnologiesCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-252-3, DPak (2 Leads + Tab), SC-63SeriesOptiMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C34A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 90μAGate Charge (Qg) (Max) @ Vgs29nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2350pF @ 100VVgs (Max)±20VFET Feature-Power Dissipation (Max)136W (Tc)Rds On (Max) @ Id, Vgs32 mOhm @ 34A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface Mount		
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Current - Continuous Drain (Id) @ 25°C 34A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 90μA Gate Charge (Qg) (Max) @ Vgs 29nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2350pF @ 100V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 136W (Tc) Rds On (Max) @ Id, Vgs 32 mOhm @ 34A, 10V Operating Temperature -55°C ~ 175°C (TJ)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) $Vgs(th)$ (Max) @ Id $4V$ @ $90\mu A$ Gate Charge (Qg) (Max) @ Vgs $29nC$ @ $10V$ Input Capacitance (Ciss) (Max) @ Vds $2350pF$ @ $100V$ Vgs (Max) $\pm 20V$ FET Feature Power Dissipation (Max) $136W$ (Tc) Rds On (Max) @ Id, Vgs 32 mOhm @ $34A$, $10V$ Operating Temperature $-55^{\circ}C \sim 175^{\circ}C$ (TJ)	Drain to Source Voltage (Vdss)	200V
Vgs(th) (Max) @ Id	Current - Continuous Drain (Id) @ 25°C	34A (Tc)
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Vgs (Max) $\pm 20 \text{V}$ FET Feature-Power Dissipation (Max) 136W (Tc) Rds On (Max) @ Id, Vgs $32 \text{ mOhm @ } 34 \text{A, } 10 \text{V}$ Operating Temperature $-55 ^{\circ}\text{C} \sim 175 ^{\circ}\text{C (TJ)}$	Gate Charge (Qg) (Max) @ Vgs	29nC @ 10V
FET Feature - Power Dissipation (Max) 136W (Tc) Rds On (Max) @ Id, Vgs 32 mOhm @ 34A, 10V Operating Temperature -55°C ~ 175°C (TJ)	Input Capacitance (Ciss) (Max) @ Vds	2350pF @ 100V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 32 mOhm @ 34A, 10V Operating Temperature -55°C ~ 175°C (TJ)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 32 mOhm @ 34A, 10V Operating Temperature $-55^{\circ}\text{C} \sim 175^{\circ}\text{C}$ (TJ)	FET Feature	-
Operating Temperature $-55^{\circ}\text{C} \sim 175^{\circ}\text{C} \text{ (TJ)}$	Power Dissipation (Max)	136W (Tc)
	Rds On (Max) @ Id, Vgs	32 mOhm @ 34A, 10V
Mounting Type Surface Mount	Operating Temperature	-55°C ~ 175°C (TJ)
	Mounting Type	Surface Mount
Supplier Device Package PG-TO252-3	Supplier Device Package	PG-TO252-3
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
Report errors?		Report errors?

IPD320N20N3GATMA1 Guarantees



Ouality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IPD320N20N3GATMA1 Payment Methods



















IPD320N20N3GATMA1 Shipping Methods













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